

Supplementary Information

A small bandgap ($3E,7E$)-3,7-bis(2-oxoindolin-3-ylidene)benzo[1,2-*b*:4,5-*b'*]difuran-2,6($3H,7H$)-dione (IBDF) based polymer semiconductor for near-infrared organic phototransistors

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Acknowledgments

The authors thank the Natural Sciences and Engineering Research Council (NSERC) of Canada for the financial support (Discovery Grants #402566-2011) of this work.

Supplementary Information

Additional data

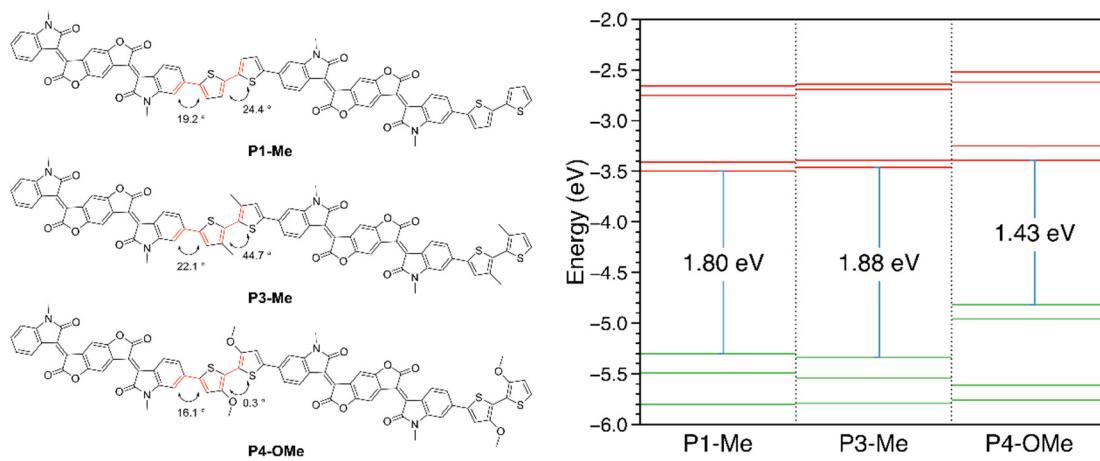


Figure S1. The molecular structures of dimers with theoretical comparison of bandgap energies and frontier energy levels for **P1-Me**, **P3-Me**, and **P4-Me**.

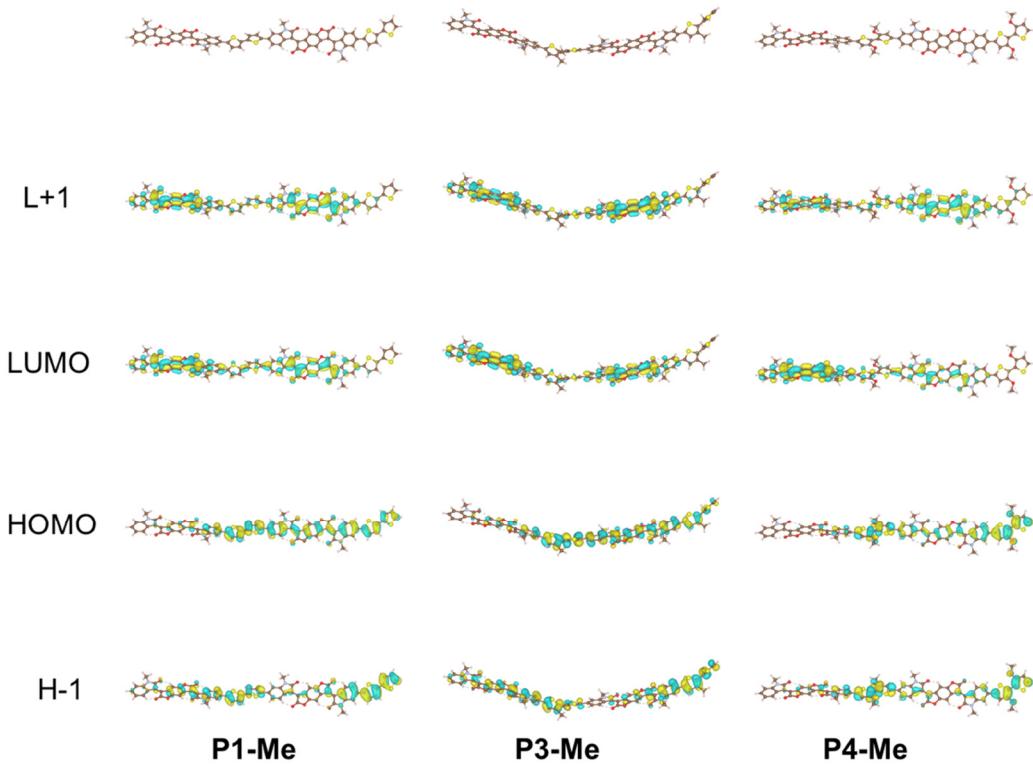


Figure S2. The optimized geometry and frontier energy levels of **P1-Me**, **P3-Me**, and **P4-Me**.

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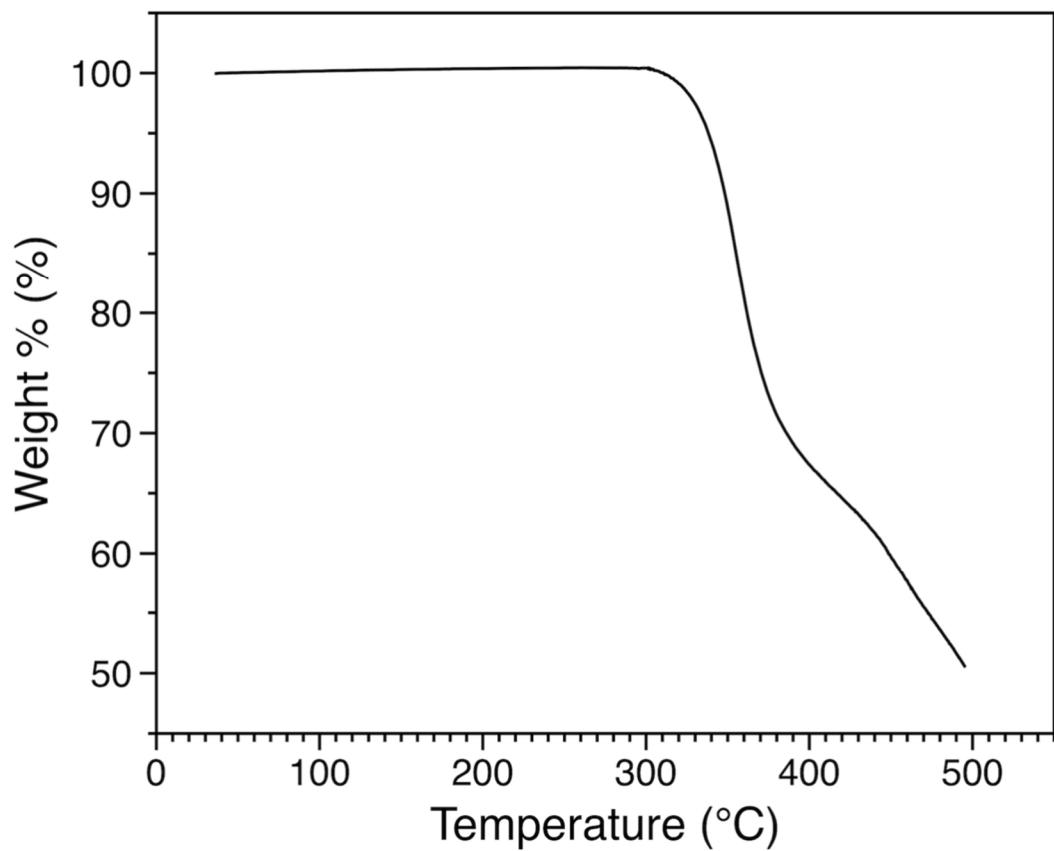


Figure S3. Thermogravimetric analysis (TGA) trace of **P4 (PIBDFBTO-HH)** with a scan rate of $10\text{ }^{\circ}\text{C min}^{-1}$ under nitrogen.

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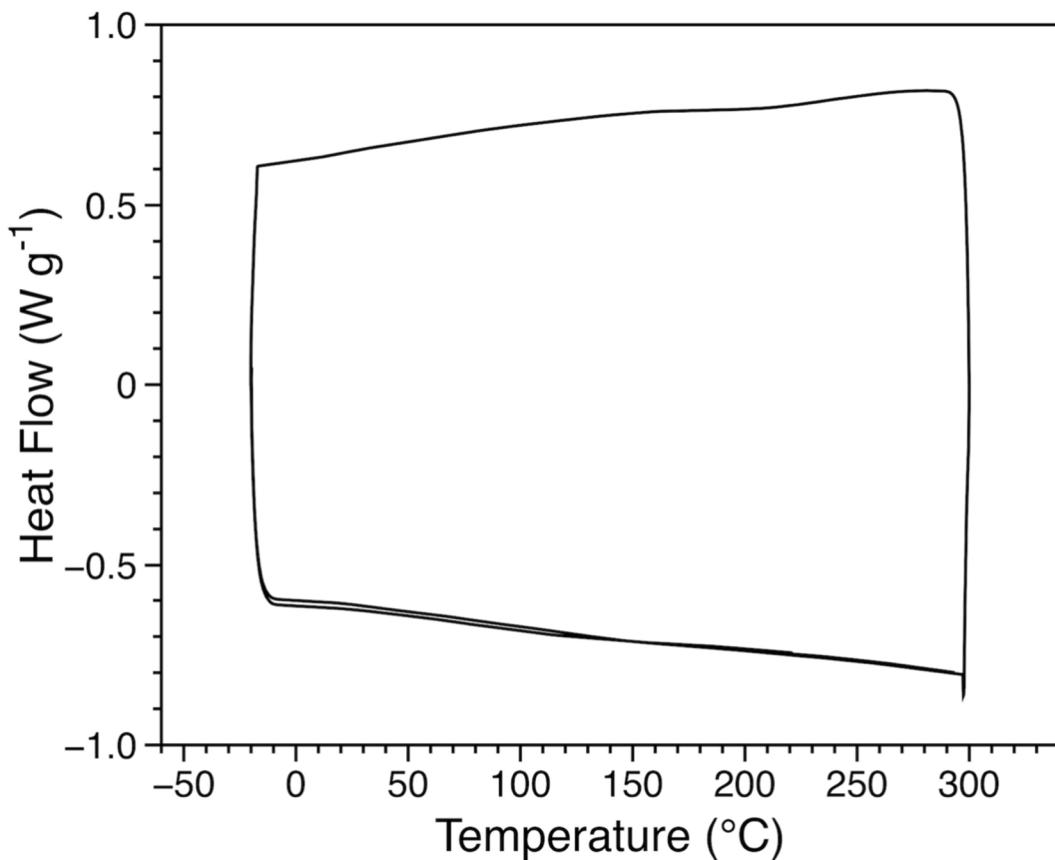


Figure S4. Differential scanning calorimetry (DSC) trace of **P4 (PIBDFBTO-HH)** with a scan rate of 20 °C min⁻¹ under nitrogen.

Supplementary Information

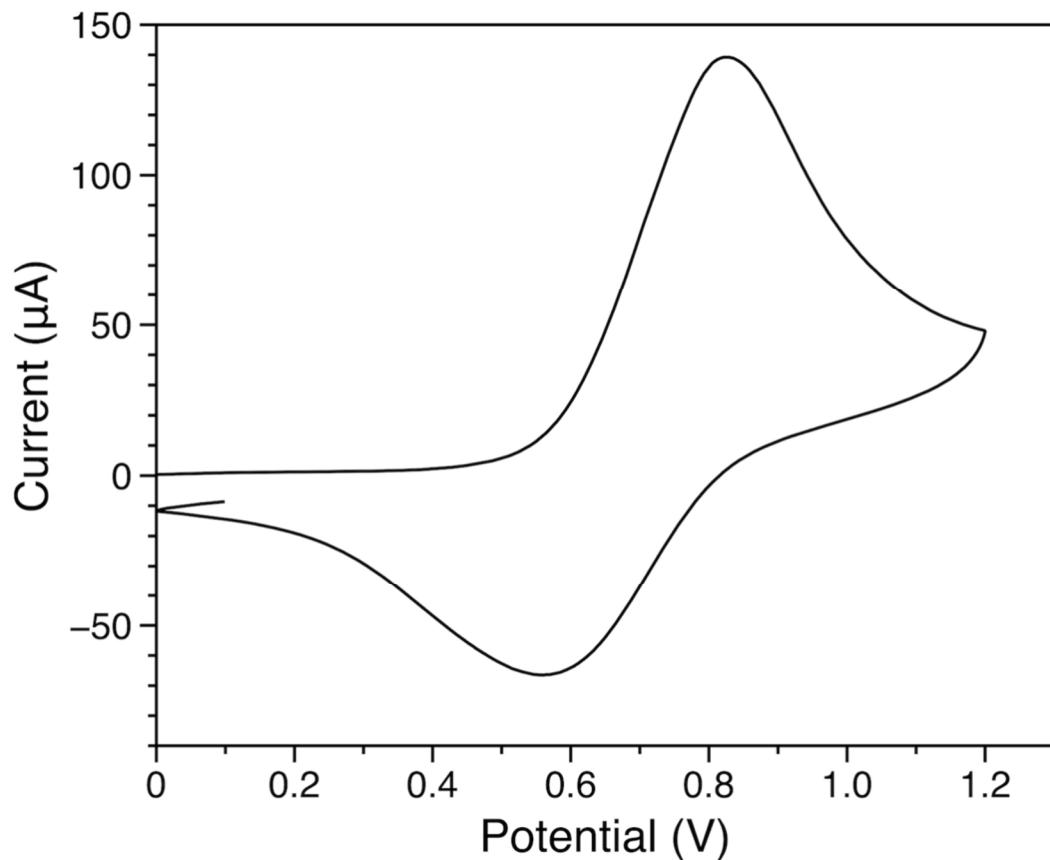


Figure S5. The cyclic voltammogram (CV) of a P4 (**PIBDFBTO-HH**) thin film measured in the oxidation cycle under nitrogen in the first oxidation cycle at a scan rate of 0.050 V s^{-1} .

Supplementary Information

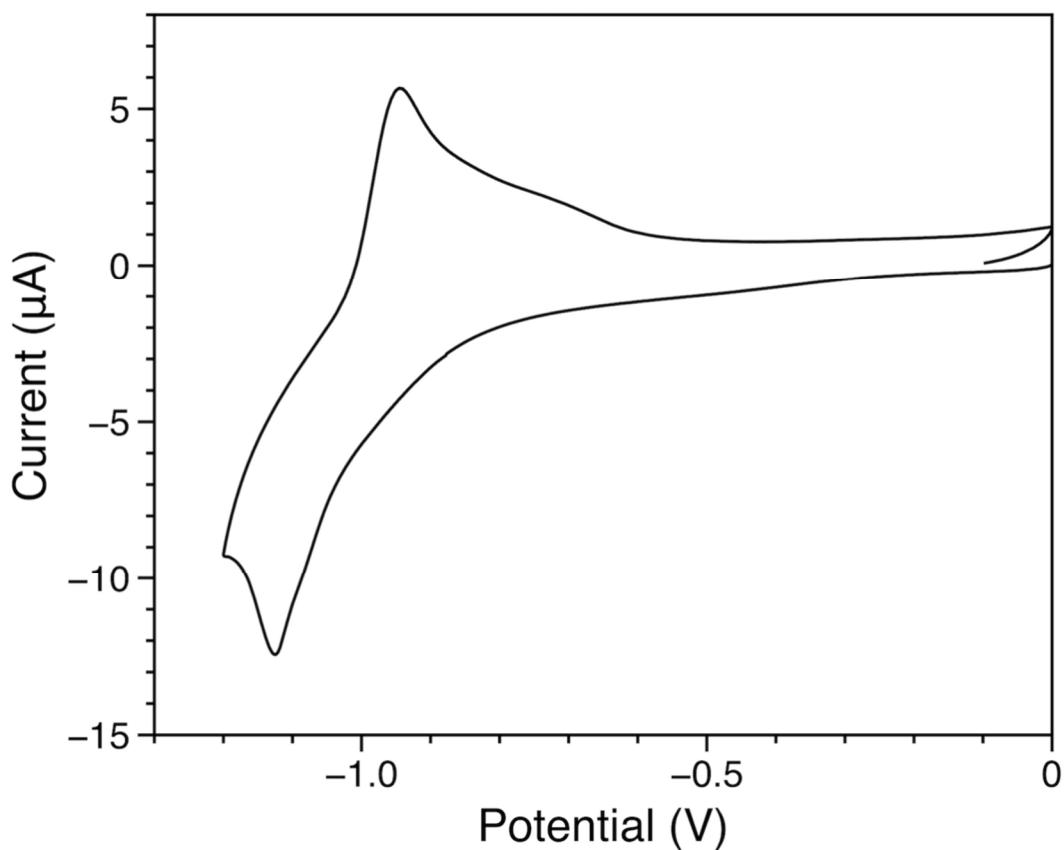


Figure S6. The cyclic voltammogram (CV) of a P4 (PIBDFBTO-HH) thin film measured in the reduction cycle under nitrogen in the first reduction cycle at a scan rate of 0.050 V s^{-1} .

Supplementary Information

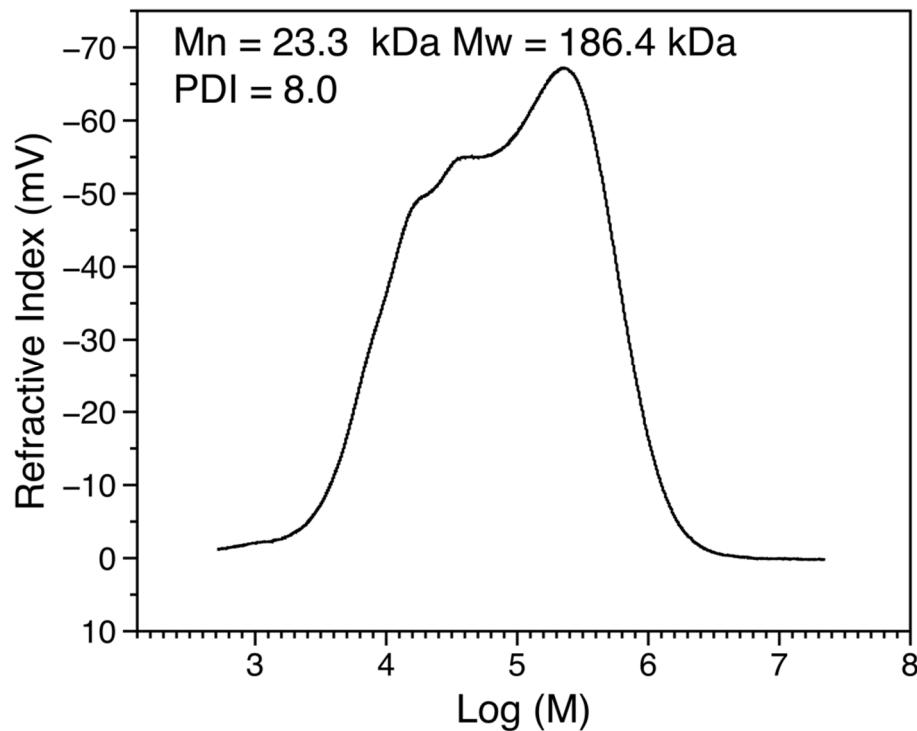


Figure S7. The molecular weight distribution of **P4** measured by HT-GPC at 140 °C.

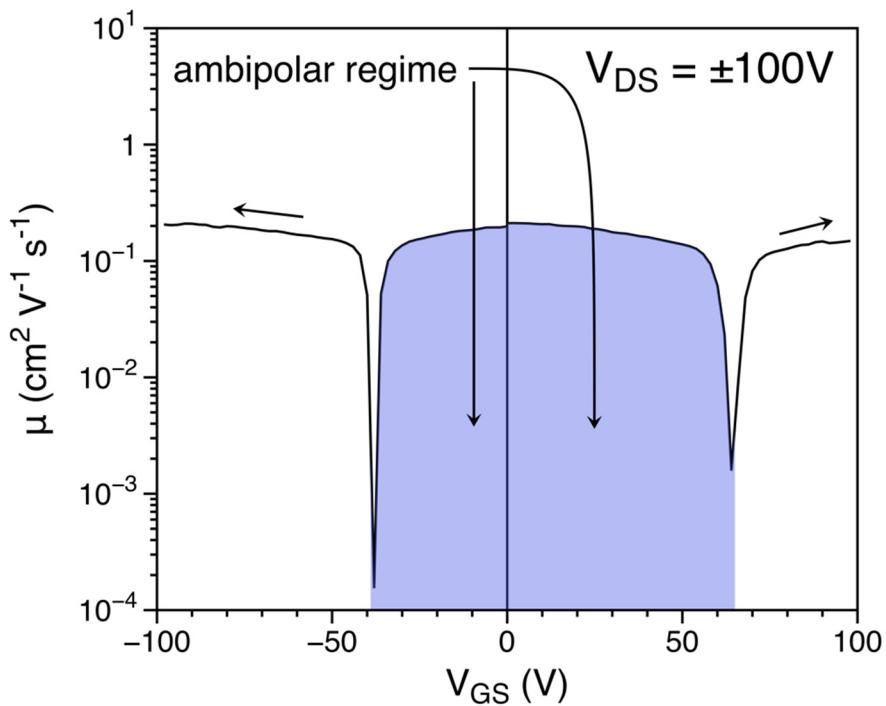


Figure S8. The mobility as a function of gate voltage (V_{GS}) for 150 °C-annealed **P4**.

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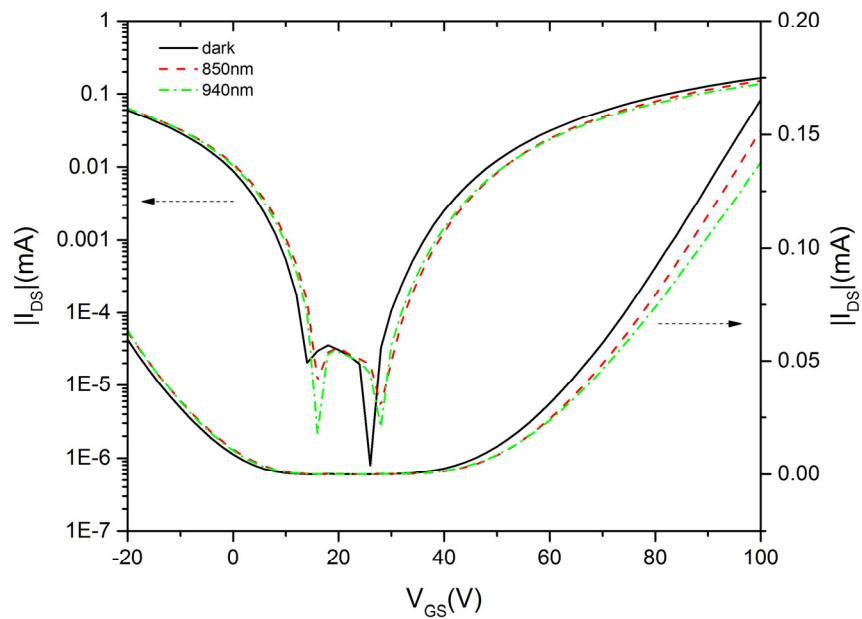


Figure S9. The transfer curves of a typical OPT based on 150 °C-annealed **P4** in the n-channel operation mode at $V_{DS} = 10$ V under illumination with 850 nm and 940 nm light sources.

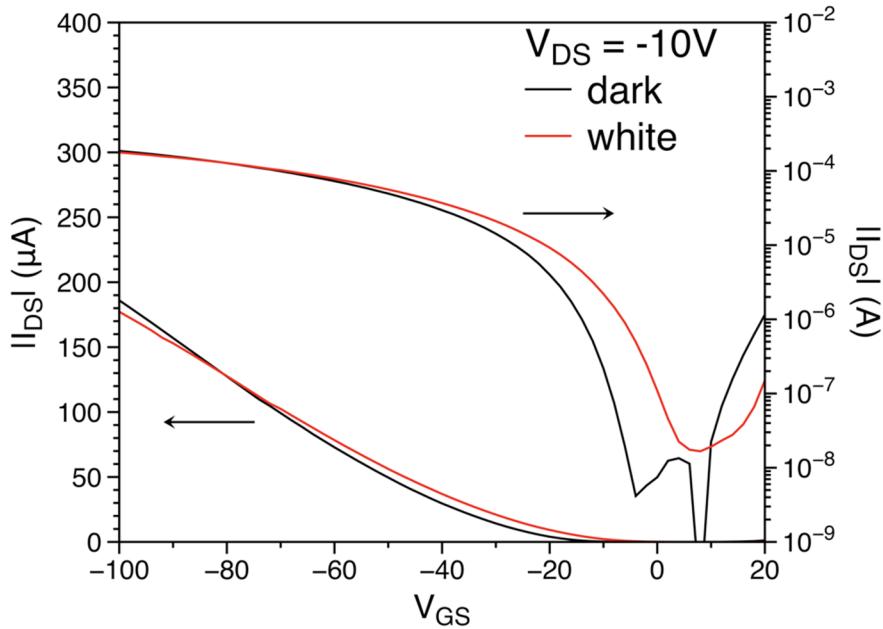


Figure S10. The transfer curves of a typical OPT based on 150 °C-annealed **P4** in the p-channel operation mode at $V_{DS} = -10$ V under illumination of a white LED (A 10W LED with a colour temperature of 3000 to 3500 K with an emission peak at 579 nm was used as the light source).¹

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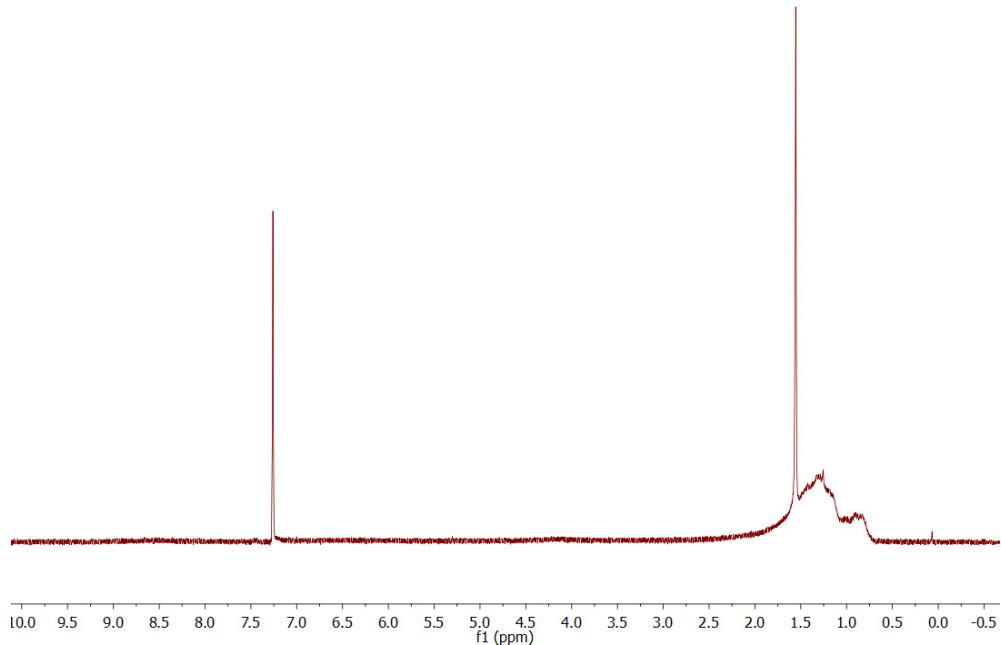


Figure S11. The 300 MHz ¹H-NMR spectrum of **P4** measured in a chloroform-d solution at room temperature.

References

1. J. T. E. Quinn, F. Haider, H. Patel, D. A. Khan, Z. Wang, and Y. Li, *J. Mater. Chem. C*, 2017, **5**, 8742-8748.